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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	TBD
				Filing Date	Herewith
				First Named Inventor	Yeo, <i>et al.</i>
				Art Unit	TBD
				Examiner Name	TBD
Sheet	1	of	1	Attorney Docket Number	TSM03-0826

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
DF	1	US-6,485,309 B1	10-15-2002	Xiang, <i>et al.</i>	
DF	2	US-6,475,874 B2	11-05-2002	Xiang, <i>et al.</i>	
DF	3	US-6,518,154 B1	02-11-2003	Buynoski, <i>et al.</i>	
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FOREIGN PATENT DOCUMENTS						
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DF	4	TAVEL, B., <i>et al.</i> , "Totally Silicided (CoSi ₂) Polysilicon: A Novel Approach To Very Low-Resistive Gate (~2Ω/□) Without Metal CMP Nor Etching" IEDM (March 2001) pp. 825-828.	
DF	5	MASZARA, W.P., <i>et al.</i> , "Transistors With Dual Work Function Metal Gates By Single Full Silicidation (FUSI) Of Polysilicon," IEDM (February 2002) pp. 367-370.	

Examiner Signature		Date Considered	4/8/06
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